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(21) International Application Number: PCT/US98/02794 (22) International Filing Date: 14 February 1998 (14.02.98) (30) Priority Data: 08/801,911 14 February 1997 (14.02.97) US (71) Applicant: EKC TECHNOLOGY, INC. [US/US]; 2520 Barrington Court, Hayward, CA 94545 (US). (71)(72) Applicant and Inventor: SMALL, Robert, J. [US/US]; 11418 Rampart Drive, Dublin, CA 94568 (US). (74) Agents: HIGGINS, Willis, E.; Cooley Godward LLP, 3000 El Camino Real, Five Palo Alto Square, Palo Alto, CA 94306-2155 (US) et al.		(81) Designated States: CN, ID, JP, KR, SG, European patent (AT, BE, CH, DE, DK, ES, FI, FR, GB, GR, IE, IT, LU, MC, NL, PT, SE). Published <i>With international search report.</i> <i>With amended claims and statement.</i>
(54) Title: POST CLEAN TREATMENT		
(57) Abstract A composition for removal of chemical residues from metal or dielectric surfaces or for chemical mechanical polishing of a copper surface is an aqueous solution with a pH between about 3.5 and about 7. The composition contains a monofunctional, difunctional or trifunctional organic acid and a buffering amount of a quaternary amine, ammonium hydroxide, hydroxylamine, hydroxylamine salt, hydrazine or hydrazine salt base. A method in accordance with the invention for removal of chemical residues from a metal or dielectric surface comprises contacting the metal or dielectric surface with the above composition for a time sufficient to remove the chemical residues. A method in accordance with the invention for chemical mechanical polishing of a copper surface comprises applying the above composition to the copper surface, and polishing the surface in the presence of the composition.		